



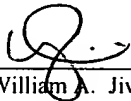
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicants : Trivedi et al.  
Serial No. : 09/808,864  
Confirm. No. : 5568  
Filed : March 15, 2001  
Title : **SUPPRESSION OF CROSS DIFFUSION AND GATE  
DEPLETION**  
Docket No. : MIO 0079 PA  
Examiner : Foong, Suk-San  
Art Unit : 2823

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

CERTIFICATE OF MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on March 4, 2003.	
 William A. Jividen	42,695 Reg. No.

AMENDMENT

This paper is being filed in response to the Office Action of February 18, 2003. Reconsideration of the present application is respectfully requested in light of the amendments and remarks below.

Attached hereto as an Appendix is a marked-up reproduction of the above-amended sections of the specification, abstract, and claims, wherein additions are underscored and deletions are stricken.

IN THE SPECIFICATION

In the specification, be amend as the following:

Please replace the paragraph on page 1, starting at line 7, with:

--Integrated circuit devices commonly employ a laminar or polysilicide structure composed of a polycrystalline silicon film and an overlying film of a metal, metal silicide, or metal nitride. In many cases, the polycrystalline silicon film comprises an N+

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